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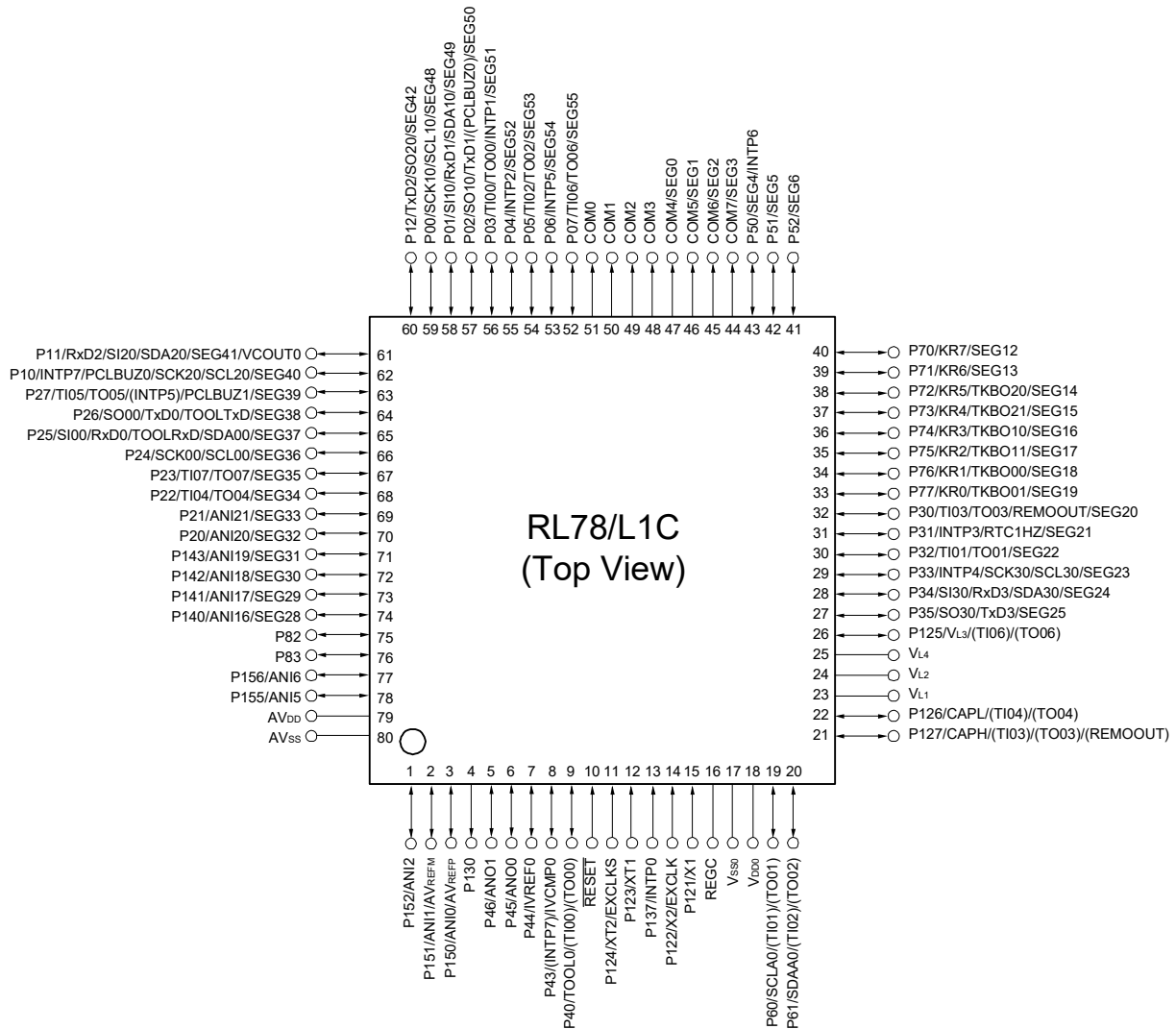
"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I ² C, LINbus, UART/USART, USB
Peripherals	LCD, LVD, POR, PWM, WDT
Number of I/O	51
Program Memory Size	192KB (192K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 3.6V
Data Converters	A/D 9x8/12b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-LQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f110mhafb-30

1.3.2 80-pin products (without USB)

- 80-pin plastic LQFP (fine pitch) (12 × 12 mm, 0.5 mm pitch)

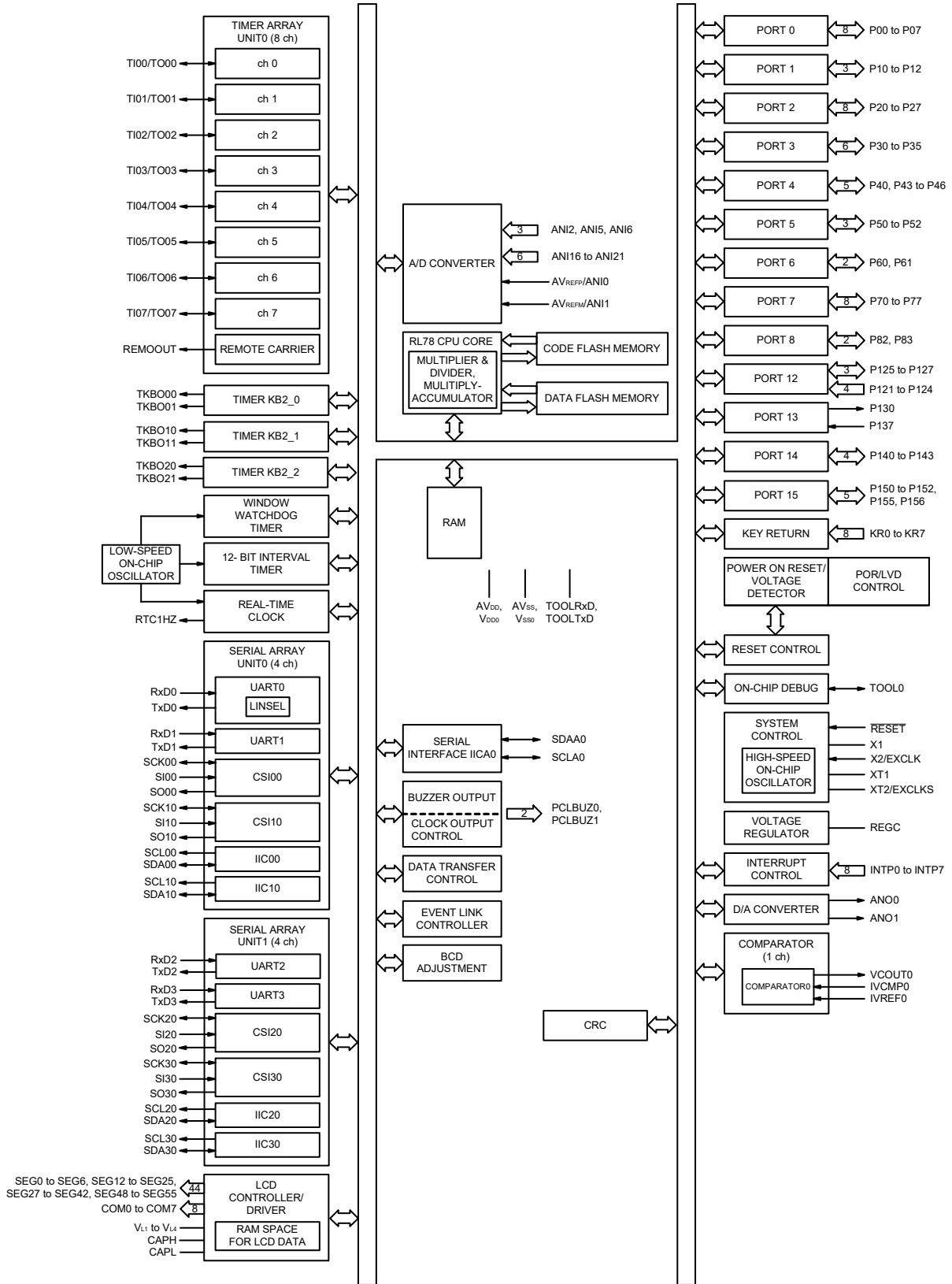


Caution Connect the REGC pin to V_{SS} pin via a capacitor (0.47 to 1 μF).

Remark 1. For pin identification, see 1.4 Pin Identification.

Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

<R> 1.5.2 80/85-pin products (without USB)



(2/2)

Item	80/85-pin		100-pin
	R5F110Mx/R5F110Nx (x = E to H, J)		R5F110Px (x = E to H, J)
Clock output/buzzer output	2		2
	<ul style="list-style-type: none"> • 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: f_{MAIN} = 20 MHz operation) • 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (Subsystem clock: f_{SUB} = 32.768 kHz operation) 		
8/12-bit resolution A/D converter	9 channels		13 channels
D/A converter	2 channels		2 channels
Comparator	1 channel		2 channels
Serial interface	<ul style="list-style-type: none"> • CSI: 1 channel/UART (UART supporting LIN-bus): 1 channel/simplified I²C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I²C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I²C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I²C: 1 channel 		
	I ² C bus	1 channel	1 channel
USB	Function	1 channel	
LCD controller/driver	Internal voltage boosting method, capacitor split method, and external resistance division method are switchable.		
	Segment signal output	44 (40) ^{Note 1}	56 (52) ^{Note 1}
	Common signal output	4 (8) ^{Note 1}	
Data transfer controller (DTC)	32 sources		33 sources
Event link controller (ELC)	Event input: 30, Event trigger output: 22		Event input: 31, Event trigger output: 22
Vectored interrupt sources	Internal	36	37
	External	9	9
Key interrupt	8		8
Reset	<ul style="list-style-type: none"> • Reset by $\overline{\text{RESET}}$ pin • Internal reset by watchdog timer • Internal reset by power-on-reset • Internal reset by voltage detector • Internal reset by illegal instruction execution ^{Note 2} • Internal reset by RAM parity error • Internal reset by illegal-memory access 		
Power-on-reset circuit	<ul style="list-style-type: none"> • Power-on-reset: 1.51 ± 0.03 V • Power-down-reset: 1.50 ± 0.03 V 		
Voltage detector	<ul style="list-style-type: none"> • Rising edge: 1.67 V to 3.13 V (12 stages) • Falling edge: 1.63 V to 3.06 V (12 stages) 		
On-chip debug function	Provided		
Power supply voltage	V _{DD} = 1.6 to 3.6 V (T _A = -40 to +85°C) V _{DD} = 2.4 to 3.6 V (T _A = -40 to +105°C)		
Operating ambient temperature	T _A = -40 to +85°C (A: Consumer applications), T _A = -40 to +105°C (G: Industrial applications)		

Note 1. The number in parentheses indicates the number of signal outputs when 8 coms are used.

Note 2. The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not is issued by emulation with the in-circuit emulator or on-chip debug emulator.

<R>

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

(TA = -40 to +85°C, 2.7 V ≤ VDD ≤ 3.6 V, VSS = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t _{KCY1}	t _{KCY1} ≥ f _{CLK/2}	2.7 V ≤ V _{DD} ≤ 3.6 V	167		250		500		ns
SCKp high-/low-level width	t _{KL1}	2.7 V ≤ V _{DD} ≤ 3.6 V		t _{KCY1/2} - 10		t _{KCY1/2} - 50		t _{KCY1/2} - 50		ns
Slp setup time (to SCKp↑) ^{Note 1}	t _{SIK1}	2.7 V ≤ V _{DD} ≤ 3.6 V		33		110		110		ns
Slp hold time (from SCKp↑) ^{Note 2}	t _{SI1}	2.7 V ≤ V _{DD} ≤ 3.6 V		10		10		10		ns
Delay time from SCKp↓ to SOp output ^{Note 3}	t _{KSO1}	C = 20 pF ^{Note 4}			10		10		10	ns

Note 1. When DAP_{mn} = 0 and CKP_{mn} = 0, or DAP_{mn} = 1 and CKP_{mn} = 1. The Slp setup time becomes “to SCKp↓” when DAP_{mn} = 0 and CKP_{mn} = 1, or DAP_{mn} = 1 and CKP_{mn} = 0.

Note 2. When DAP_{mn} = 0 and CKP_{mn} = 0, or DAP_{mn} = 1 and CKP_{mn} = 1. The Slp hold time becomes “from SCKp↓” when DAP_{mn} = 0 and CKP_{mn} = 1, or DAP_{mn} = 1 and CKP_{mn} = 0.

Note 3. When DAP_{mn} = 0 and CKP_{mn} = 0, or DAP_{mn} = 1 and CKP_{mn} = 1. The delay time to SOp output becomes “from SCKp↑” when DAP_{mn} = 0 and CKP_{mn} = 1, or DAP_{mn} = 1 and CKP_{mn} = 0.

Note 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the Slp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM number (g = 2)

Remark 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKS_{mn} bit of serial mode register mn (SMR_{mn}). m: Unit number, n: Channel number (mn = 00))

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input)
(TA = -40 to +85°C, 1.6 V ≤ VDD ≤ 3.6 V, VSS = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note 5	tkCY2	2.7 V ≤ VDD < 3.6 V	fMCK > 16 MHz	8/fMCK	—	—	—	—	ns	
			fMCK ≤ 16 MHz	6/fMCK	—	6/fMCK	—	6/fMCK	ns	
		2.4 V ≤ VDD < 3.6 V		6/fMCK and 500	—	6/fMCK and 500	—	6/fMCK and 500	ns	
		1.8 V ≤ VDD < 3.6 V		—	—	6/fMCK and 750	—	6/fMCK and 750	ns	
		1.6 V ≤ VDD < 3.6 V		—	—	—	—	6/fMCK and 1500	ns	
SCKp high-/low-level width	tkH2, tkL2	2.7 V ≤ VDD ≤ 3.6 V		tkCY2/2 - 8	—	tkCY2/2 - 8	—	tkCY2/2 - 8	ns	
		1.8 V ≤ VDD ≤ 3.6 V		—	—	tkCY2/2 - 18	—	tkCY2/2 - 18	ns	
		1.6 V ≤ VDD ≤ 3.6 V		—	—	—	—	tkCY1/2 - 66	ns	
Slp setup time (to SCKp↑) Note 1	tsIK2	2.7 V ≤ VDD ≤ 3.6 V		1/fMCK + 20	—	1/fMCK + 30	—	1/fMCK + 30	ns	
		2.4 V ≤ VDD ≤ 3.6 V		1/fMCK + 30	—	1/fMCK + 30	—	1/fMCK + 30	ns	
		1.8 V ≤ VDD < 3.6 V		—	—	1/fMCK + 30	—	1/fMCK + 30	ns	
		1.6 V ≤ VDD < 3.6 V		—	—	—	—	1/fMCK + 40	ns	
Slp hold time (from SCKp↑) Note 2	tkSI2	2.4 V ≤ VDD < 3.6 V		1/fMCK + 31	—	1/fMCK + 31	—	1/fMCK + 31	ns	
		1.8 V ≤ VDD < 3.6 V		—	—	1/fMCK + 31	—	1/fMCK + 31	ns	
		1.6 V ≤ VDD < 3.6 V		—	—	—	—	1/fMCK + 250	ns	
Delay time from SCKp↓ to SOp output Note 3	tkSO2	C = 30 pF Note 4	2.7 V ≤ VDD ≤ 3.6 V	—	2/fMCK + 44	—	2/fMCK + 110	—	2/fMCK + 110	ns
			2.4 V ≤ VDD < 3.6 V	—	2/fMCK + 75	—	2/fMCK + 110	—	2/fMCK + 110	ns
			1.8 V ≤ VDD < 3.6 V	—	—	—	2/fMCK + 110	—	2/fMCK + 110	ns
			1.6 V ≤ VDD < 3.6 V	—	—	—	—	—	2/fMCK + 220	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SOp output lines.

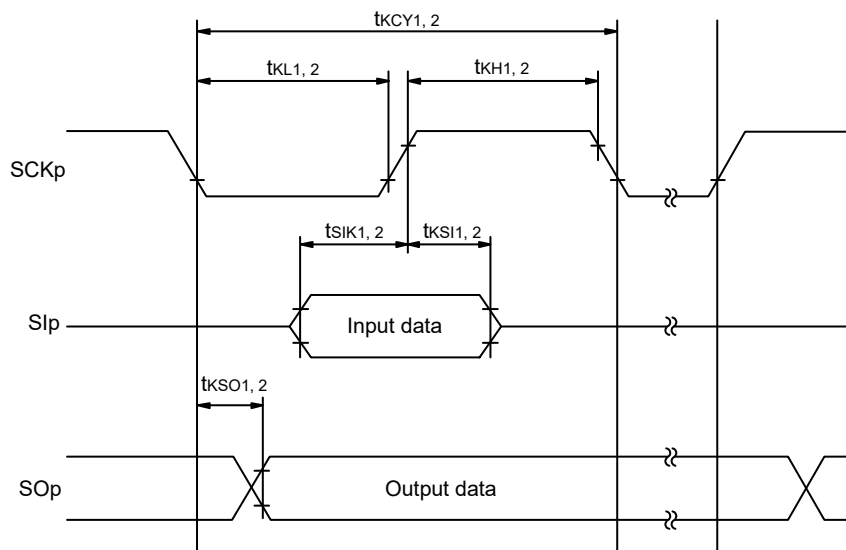
Note 5. The maximum transfer rate when using the SNOOZE mode is 1 Mbps.

Caution Select the normal input buffer for the Slp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

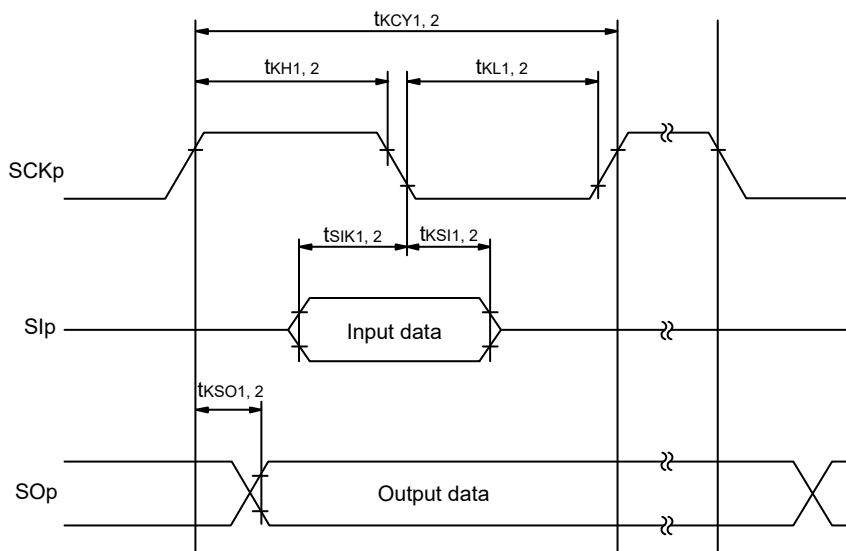
Remark 1. p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0 to 3)

Remark 2. fMCK: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

**CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)**



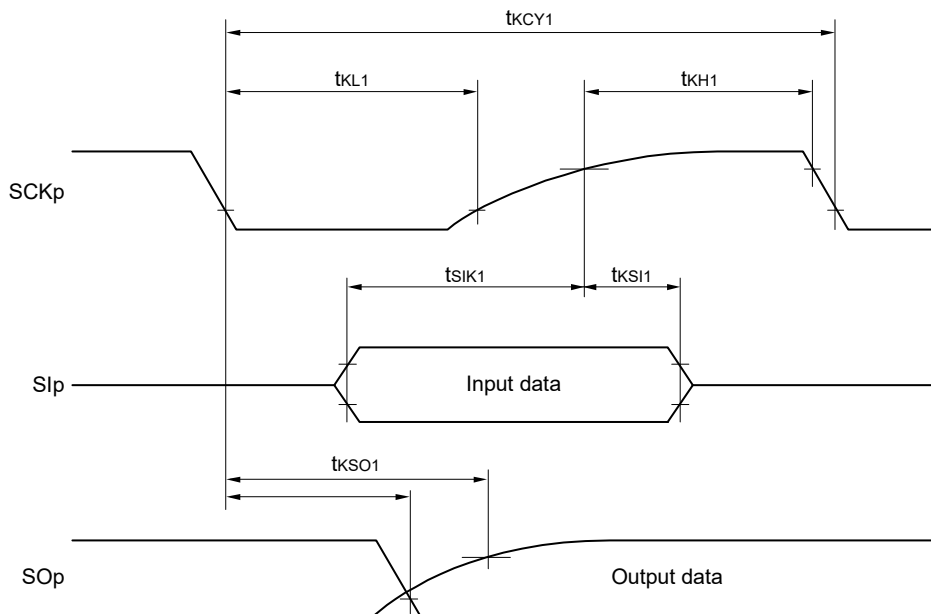
**CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)**



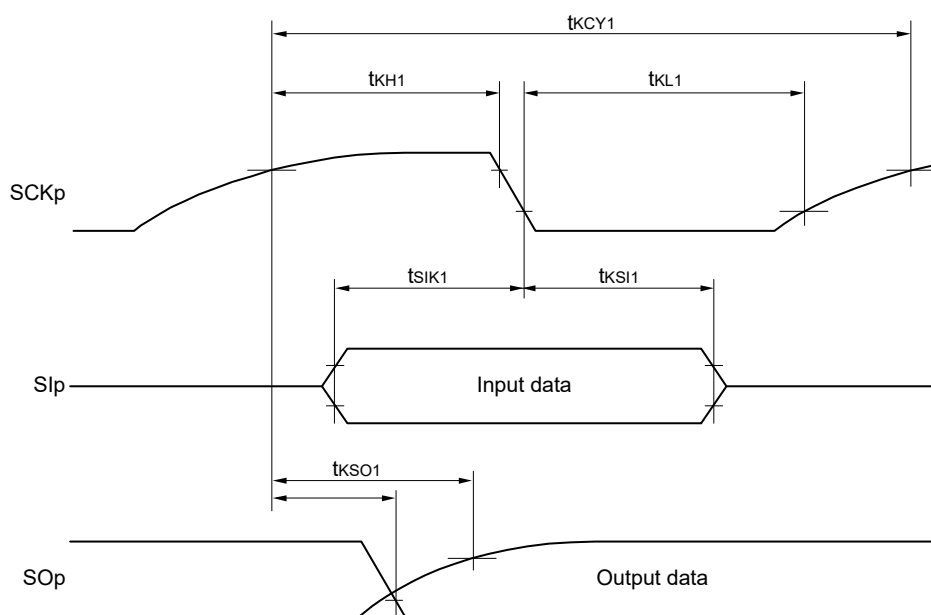
Remark 1. p: CSI number (p = 00, 10, 20, 30)

Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

**CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)**

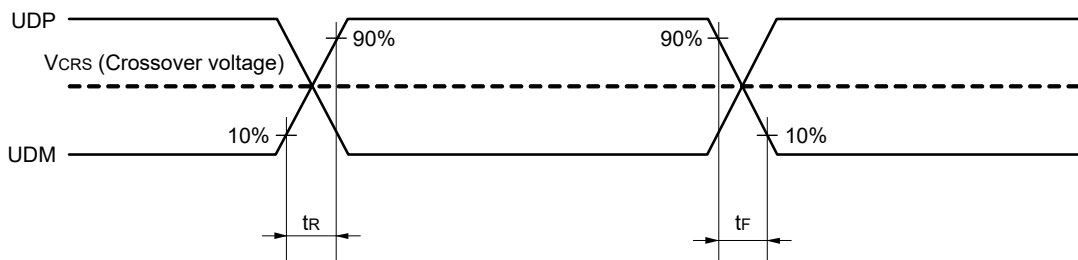


**CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)**



Remark p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3),
g: PIM and POM number (g = 0 to 3)

Timing of UDP and UDM



(2) BC standard

(TA = -40 to +85°C, 4.35 V ≤ UVBUS ≤ 5.25 V, 2.4 V ≤ VDD ≤ 3.6 V, VSS = 0 V, HS (High-speed main) mode only)

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
USB standard BC1.2	UDP sink current	IDP_SINK		25	100	175	μA
	UDM sink current	IDM_SINK		25	100	175	μA
	DCD source current	IDP_SRC		7	10	13	μA
	Data detection voltage	VDAT_REF		0.25	0.325	0.4	V
	UDP source voltage	VDP_SRC	Output current 250 μA	0.5	0.6	0.7	V
	UDM source voltage	VDM_SRC	Output current 250 μA	0.5	0.6	0.7	V

(5) When reference voltage (+) = AVDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = AVSS (ADREFM = 0), conversion target: ANI16 to ANI21, internal reference voltage, temperature sensor output voltage

(TA = -40 to +85°C, 1.6 V ≤ VDD ≤ 3.6 V, 1.6 V ≤ AVDD = VDD ≤ 3.6 V, VSS = 0 V, AVSS = 0 V, Reference voltage (+) = AVDD, Reference voltage (-) = AVSS = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES		2.4 V ≤ AVDD ≤ 3.6 V	8		12	bit
			1.8 V ≤ AVDD ≤ 3.6 V	8		10 Note 1	
			1.6 V ≤ AVDD ≤ 3.6 V	8 Note 2			
Overall error Note 3	AINL	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±8.5	LSB
		10-bit resolution	1.8 V ≤ AVDD ≤ 3.6 V			±6.0	
		8-bit resolution	1.6 V ≤ AVDD ≤ 3.6 V			±3.5	
Conversion time	tCONV	ADTYP = 0, 12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V	4.125			μs
		ADTYP = 0, 10-bit resolution Note 1	1.8 V ≤ AVDD ≤ 3.6 V	9.5			
		ADTYP = 0, 8-bit resolution Note 2	1.6 V ≤ AVDD ≤ 3.6 V	57.5			
		ADTYP = 1, 8-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V	3.3125			
			1.8 V ≤ AVDD ≤ 3.6 V	7.875			
Zero-scale error Note 3	Ezs	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±8.0	LSB
		10-bit resolution	1.8 V ≤ AVDD ≤ 3.6 V			±5.5	
		8-bit resolution	1.6 V ≤ AVDD ≤ 3.6 V			±3.0	
Full-scale error Note 3	EFS	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±8.0	LSB
		10-bit resolution	1.8 V ≤ AVDD ≤ 3.6 V			±5.5	
		8-bit resolution	1.6 V ≤ AVDD ≤ 3.6 V			±3.0	
Integral linearity error Note 3	ILE	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±3.5	LSB
		10-bit resolution	1.8 V ≤ AVDD ≤ 3.6 V			±2.5	
		8-bit resolution	1.6 V ≤ AVDD ≤ 3.6 V			±1.5	
Differential linearity error Note 3	DLE	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±2.5	LSB
		10-bit resolution	1.8 V ≤ AVDD ≤ 3.6 V			±2.5	
		8-bit resolution	1.6 V ≤ AVDD ≤ 3.6 V			±2.0	
Analog input voltage	VAIN			0		AVDD	V
		Internal reference voltage (2.4 V ≤ VDD ≤ 3.6 V, HS (high-speed main) mode)		VBGR Note 4			
		Temperature sensor output voltage (2.4 V ≤ VDD ≤ 3.6 V, HS (high-speed main) mode)		VTMP25 Note 4			

Note 1. Cannot be used for lower 2 bits of ADCR register

Note 2. Cannot be used for lower 4 bits of ADCR register

Note 3. Excludes quantization error (±1/2 LSB).

Note 4. Refer to 2.6.2 Temperature sensor, internal reference voltage output characteristics.

Caution Always use AVDD pin with the same potential as the VDD pin.

2.8.2 Internal voltage boosting method

(1) 1/3 bias method

(TA = -40 to +85°C, 1.8 V ≤ VDD ≤ 3.6 V, VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
LCD output voltage variation range	VL1	C1 to C4 ^{Note 1} = 0.47 μF ^{Note 2}	VLCD = 04H	0.90	1.00	1.08	V
			VLCD = 05H	0.95	1.05	1.13	V
			VLCD = 06H	1.00	1.10	1.18	V
			VLCD = 07H	1.05	1.15	1.23	V
			VLCD = 08H	1.10	1.20	1.28	V
			VLCD = 09H	1.15	1.25	1.33	V
			VLCD = 0AH	1.20	1.30	1.38	V
			VLCD = 0BH	1.25	1.35	1.43	V
			VLCD = 0CH	1.30	1.40	1.48	V
			VLCD = 0DH	1.35	1.45	1.53	V
			VLCD = 0EH	1.40	1.50	1.58	V
			VLCD = 0FH	1.45	1.55	1.63	V
			VLCD = 10H	1.50	1.60	1.68	V
			VLCD = 11H	1.55	1.65	1.73	V
VLCD = 12H	1.60	1.70	1.78	V			
VLCD = 13H	1.65	1.75	1.83	V			
Doubler output voltage	VL2	C1 to C4 ^{Note 1} = 0.47 μF	2 VL1 - 0.1	2 VL1	2 VL1	V	
Tripler output voltage	VL3	C1 to C4 ^{Note 1} = 0.47 μF	3 VL1 - 0.15	3 VL1	3 VL1	V	
Reference voltage setup time ^{Note 2}	tVWAIT1		5			ms	
Voltage boost wait time ^{Note 3}	tVWAIT2	C1 to C4 ^{Note 1} = 0.47 μF	500			ms	

Note 1. This is a capacitor that is connected between voltage pins used to drive the LCD.

C1: A capacitor connected between CAPH and CAPL

C2: A capacitor connected between VL1 and GND

C3: A capacitor connected between VL2 and GND

C4: A capacitor connected between VL4 and GND

C1 = C2 = C3 = C4 = 0.47 μF ± 30%

Note 2. This is the time required to wait from when the reference voltage is specified by using the VLCD register (or when the internal voltage boosting method is selected (by setting the MDSET1 and MDSET0 bits of the LCDM0 register to 01B) if the default value reference voltage is used) until voltage boosting starts (VLCON = 1).

Note 3. This is the wait time from when voltage boosting is started (VLCON = 1) until display is enabled (LCDON = 1).

3. ELECTRICAL SPECIFICATIONS (G: INDUSTRIAL APPLICATIONS TA = -40 to +105°C)

This chapter describes the following electrical specifications.

Target products G: Industrial applications TA = -40 to +105°C

R5F110xxGxx, R5F111xxGxx

Caution 1. The RL78 microcontroller has an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.

Caution 2. The pins mounted depend on the product. Refer to 2.1 Port Function to 2.2.1 With functions for each product in the RL78/L1C User's Manual.

Caution 3. Please contact Renesas Electronics sales office for derating of operation under TA = +85°C to +105°C. Derating is the systematic reduction of load for the sake of improved reliability.

Remark When the RL78 microcontroller is used in the range of TA = -40 to +85°C, see **2. ELECTRICAL SPECIFICATIONS (TA = -40 to +85°C)**.

The following functions differ between the products "G: Industrial applications (TA = -40 to +105°C)" and the products "A: Consumer applications and G: Industrial applications (when used in the range of TA = -40 to +85°C)".

Parameter	A: Consumer applications	G: Industrial applications
Operating ambient temperature	TA = -40 to +85°C	TA = -40 to +105°C
Operating mode Operating voltage range	HS (high-speed main) mode: 2.7 V ≤ VDD ≤ 3.6 V@1 MHz to 24 MHz 2.4 V ≤ VDD ≤ 3.6 V@1 MHz to 16 MHz LS (low-speed main) mode: 1.8 V ≤ VDD ≤ 3.6 V@1 MHz to 8 MHz LV (low-voltage main) mode: 1.6 V ≤ VDD ≤ 3.6 V@1 MHz to 4 MHz	HS (high-speed main) mode only: 2.7 V ≤ VDD ≤ 3.6 V@1 MHz to 24 MHz 2.4 V ≤ VDD ≤ 3.6 V@1 MHz to 16 MHz
High-speed on-chip oscillator clock accuracy	1.8 V ≤ VDD ≤ 3.6 V: ±1.0% @ TA = -20 to +85°C ±1.5% @ TA = -40 to -20°C 1.6 V ≤ VDD ≤ 1.8 V: ±5.0% @ TA = -20 to +85°C ±5.5% @ TA = -40 to -20°C	2.4 V ≤ VDD ≤ 3.6 V: ±2.0% @ TA = +85 to +105°C ±1.0% @ TA = -20 to +85°C ±1.5% @ TA = -40 to -20°C
Serial array unit	UART CSI: fCLK/4 Simplified I ² C communication	UART CSI: fCLK/4 Simplified I ² C communication
IICA	Normal mode Fast mode Fast mode plus	Normal mode Fast mode
Voltage detector	• Rise detection: 1.67 V to 3.13 V (12 levels) • Fall detection: 1.63 V to 3.06 V (12 levels)	• Rise detection: 2.61 V to 3.13 V (6 levels) • Fall detection: 2.55 V to 3.06 V (6 levels)

Remark The electrical characteristics of the products G: Industrial applications (TA = -40 to +105°C) are different from those of the products "A: Consumer applications". For details, refer to 3.1 to 3.12.

Absolute Maximum Ratings (TA = 25°C)**(3/3)**

Parameter	Symbols	Conditions		Ratings	Unit
Output current, high	IOH1	Per pin	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P130, P140 to P143	-40	mA
		Total of all pins -170 mA	P40 to P46	-70	mA
			P00 to P07, P10 to P17, P20 to P27, P30 to P37, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P130, P140 to P143	-100	mA
	IOH2	Per pin	P150 to P156	-0.1	mA
		Total of all pins		-0.7	mA
	IOH3	Per pin	UDP, UDM	-3	mA
Output current, low	IOL1	Per pin	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P60, P61, P70 to P77, P80 to P83, P125 to P127, P130, P140 to P143	40	mA
		Total of all pins 170 mA	P40 to P46	70	mA
			P00 to P07, P10 to P17, P20 to P27, P30 to P37, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P130, P140 to P143	100	mA
	IOL2	Per pin	P150 to P156	0.4	mA
		Total of all pins		2.8	mA
	IOL3	Per pin	UDP, UDM	3	mA
Operating ambient temperature	TA	In normal operation mode		-40 to +105	°C
		In flash memory programming mode		-40 to +105	
Storage temperature	T _{stg}			-65 to +150	°C

<R>

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(TA = -40 to +105°C, 2.4 V ≤ AVDD = VDD ≤ 3.6 V, VSS = 0 V)

<R>

Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Output current, IOL Note 1	IOL1	Per pin for P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P130, P140 to P143			8.5 Note 2	mA
					15.0 Note 2	mA
		Total of P40 to P46, P130 (When duty ≤ 70% Note 3)	2.7 V ≤ VDD ≤ 3.6 V		15.0	mA
			2.4 V ≤ VDD < 2.7 V		9.0	mA
		Total of P00 to P07, P10 to P17, P20 to P27, P30 to P37, P50 to P57, P60, P61, P70 to P77, P80 to P83, P125 to P127, P140 to P143 (When duty ≤ 70% Note 3)	2.7 V ≤ VDD ≤ 3.6 V		35.0	mA
			2.4 V ≤ VDD < 2.7 V		20.0	mA
	Total of all pins (When duty ≤ 70% Note 3)			50.0	mA	
	IOL2	Per pin for P150 to P156			0.4 Note 2	mA
Total of all pins			2.4 V ≤ VDD ≤ 3.6 V		2.8	mA

Note 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the VSS pin.

Note 2. However, do not exceed the total current value.

Note 3. Specification under conditions where the duty factor ≤ 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression

(when changing the duty factor from 70% to n%).

• Total output current of pins = (IOL × 0.7)/(n × 0.01)

<Example> Where n = 80% and IOL = 10.0 mA

Total output current of pins = (10.0 × 0.7)/(80 × 0.01) ≈ 8.7 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

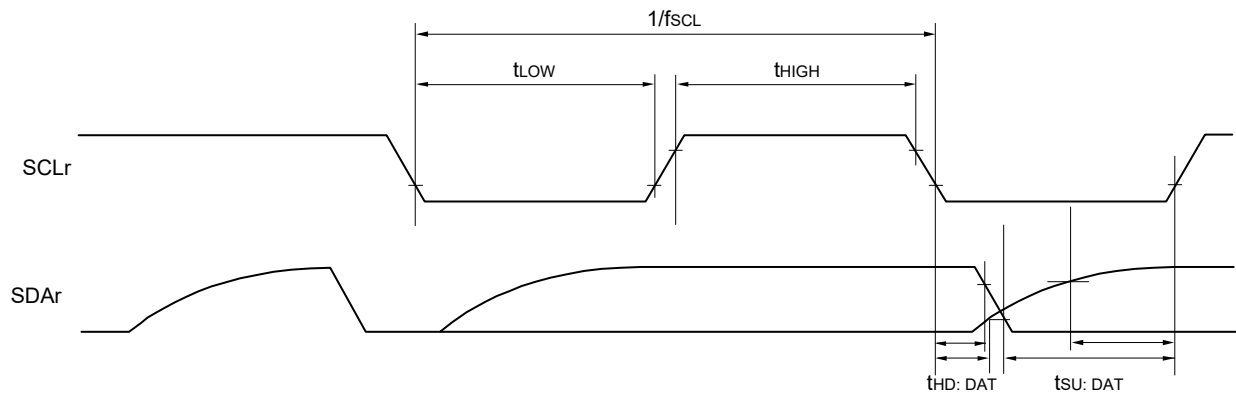
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(TA = -40 to +105°C, 2.4 V ≤ AVDD = VDD ≤ 3.6 V, VSS = 0 V)

Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit		
Input leakage current, high	LIH1	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P60, P61, P70 to P77, P80 to P83, P125 to P127, P137, P140 to P143, $\overline{\text{RESET}}$	Vi = VDD			1	μA	
	LIH2	P20, P21, P140 to P143	Vi = VDD			1	μA	
	LIH3	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	Vi = VDD	In input port or external clock input			1	μA
				In resonator connection			10	μA
LIH4	P150 to P156	Vi = AVDD			1	μA		
Input leakage current, low	LIIL1	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P60, P61, P70 to P77, P80 to P83, P125 to P127, P137, P140 to P143, $\overline{\text{RESET}}$	Vi = VSS			-1	μA	
	LIIL2	P20, P21, P140 to P143	Vi = VSS			-1	μA	
	LIIL3	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	Vi = VSS	In input port or external clock input			-1	μA
				In resonator connection			-10	μA
LIIL4	P150 to P156	Vi = AVSS			-1	μA		
On-chip pull-up resistance	RU1	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P50 to P57, P70 to P77, P140 to P143, P125 to P127	Vi = VSS	2.4 V ≤ VDD ≤ 3.6 V	10	20	100	kΩ
	RU2	P40 to P46, P80 to P83	Vi = VSS		10	20	100	kΩ

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

- Note 1.** Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or VSS. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the LCD controller/driver, A/D converter, D/A converter, comparator, LVD circuit, USB 2.0 function module, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2.** During HALT instruction execution by flash memory.
- Note 3.** When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 4.** When high-speed system clock and subsystem clock are stopped.
- Note 5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the real-time clock 2 is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
- Note 6.** Not including the current flowing into the real-time clock 2, 12-bit interval timer, and watchdog timer.
- Note 7.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 HS (high-speed main) mode: $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}@1\text{ MHz to }24\text{ MHz}$
 $2.4\text{ V} \leq V_{DD} \leq 3.6\text{ V}@1\text{ MHz to }16\text{ MHz}$
- Note 8.** Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remark 1.** fMX: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2.** fHOCO: High-speed on-chip oscillator clock frequency (48 MHz max.)
- Remark 3.** fIH: Main system clock source frequency when the high-speed on-chip oscillator clock divided 1, 2, 4, or 8, or the PLL clock divided by 2, 4, or 8 is selected (24 MHz max.)
- Remark 4.** fSUB: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5.** Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

Simplified I²C mode serial transfer timing (during communication at same potential)

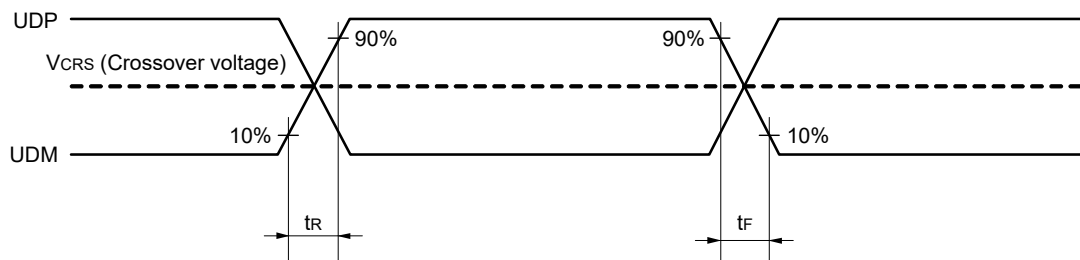
Remark 1. $R_b[\Omega]$: Communication line (SDAr) pull-up resistance, $C_b[F]$: Communication line (SDAr, SCLr) load capacitance

Remark 2. r: IIC number (r = 00, 10, 20, 30), g: PIM number (g = 0 to 3),
h: POM number (h = 0 to 3)

Remark 3. f_{MCK} : Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1),
n: Channel number (n = 0 to 3), mn = 00 to 03, 10 to 13)

Timing of UDP and UDM



(2) BC standard

(TA = -40 to +105°C, 4.35 V ≤ UVBUS ≤ 5.25 V, 2.4 V ≤ VDD ≤ 3.6 V, VSS = 0 V)

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
USB standard BC1.2	UDP sink current	IDP_SINK		25	100	175	μA
	UDM sink current	IDM_SINK		25	100	175	μA
	DCD source current	IDP_SRC		7	10	13	μA
	Data detection voltage	VDAT_REF		0.25	0.325	0.4	V
	UDP source voltage	VDP_SRC	Output current 250 μA	0.5	0.6	0.7	V
	UDM source voltage	VDM_SRC	Output current 250 μA	0.5	0.6	0.7	V

3.8 LCD Characteristics

3.8.1 Resistance division method

(1) Static display mode

(TA = -40 to +105°C, VL4 (MIN.) ≤ VDD ≤ 3.6 V, VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	VL4		2.0		VDD	V

(2) 1/2 bias method, 1/4 bias method

(TA = -40 to +105°C, VL4 (MIN.) ≤ VDD ≤ 3.6 V, VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	VL4		2.7		VDD	V

(3) 1/3 bias method

(TA = -40 to +105°C, VL4 (MIN.) ≤ VDD ≤ 3.6 V, VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	VL4		2.5		VDD	V

3.8.3 Capacitor split method

(1) 1/3 bias method

(TA = -40 to +105°C, 2.4 V ≤ VDD ≤ 3.6 V, VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
VL4 voltage	VL4	C1 to C4 = 0.47 μF Note 2		VDD		V
VL2 voltage	VL2	C1 to C4 = 0.47 μF Note 2	2/3 VL4 - 0.07	2/3 VL4	2/3 VL4 + 0.07	V
VL1 voltage	VL1	C1 to C4 = 0.47 μF Note 2	1/3 VL4 - 0.08	1/3 VL4	1/3 VL4 + 0.08	V
Capacitor split wait time Note 1	tVWAIT		100			ms

Note 1. This is the wait time from when voltage bucking is started (VLCON = 1) until display is enabled (LCDON = 1).

Note 2. This is a capacitor that is connected between voltage pins used to drive the LCD.

C1: A capacitor connected between CAPH and CAPL

C2: A capacitor connected between VL1 and GND

C3: A capacitor connected between VL2 and GND

C4: A capacitor connected between VL4 and GND

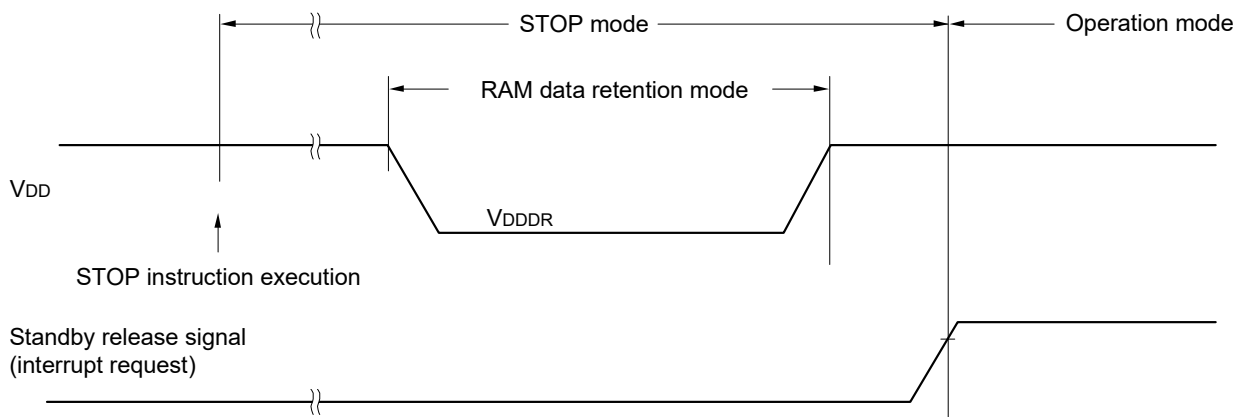
C1 = C2 = C3 = C4 = 0.47 μF±30%

3.9 RAM Data Retention Characteristics

(TA = -40 to +105°C, VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.44 Note		3.6	V

Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



3.10 Flash Memory Programming Characteristics

(TA = -40 to +105°C, 2.4 V ≤ VDD ≤ 3.6 V, VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	fCLK	2.4 V ≤ VDD ≤ 3.6 V	1		24	MHz
Number of code flash rewrites Notes 1, 2, 3	C _{erwr}	Retained for 20 years TA = 85°C ^{Note 4}	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 year TA = 25°C		1,000,000		
		Retained for 5 years TA = 85°C ^{Note 4}	100,000			
		Retained for 20 years TA = 85°C ^{Note 4}	10,000			

Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

Note 2. When using flash memory programmer and Renesas Electronics self programming library

Note 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

Note 4. This temperature is the average value at which data are retained.

3.11 Dedicated Flash Memory Programmer Communication (UART)

(TA = -40 to +105°C, 2.4 V ≤ VDD ≤ 3.6 V, VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps